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## **CLAIMS**

A positive photoresist composition comprising an alkali-soluble novolak resin
 (A) containing a structural unit (a1) represented by a general formula (I) shown below:

$$\begin{array}{c|c}
0 & R^1 & OH \\
\hline
 & H_2 \\
\hline
 & II & C
\end{array}$$
(I)

[wherein, R<sup>1</sup> represents an alkylene group of 1 to 5 carbon atoms, R<sup>2</sup> represents a hydrogen atom, a hydroxyl group, or an alkyl group of 1 to 4 carbon atoms, and m represents an integer of 1 to 3], and a structural unit (a2) represented by a general formula (II) shown below:

[wherein, R<sup>3</sup> represents a hydrogen atom, a hydroxyl group, or an alkyl group of 1 to 4 carbon atoms, and n represents an integer of 1 to 3], and a photosensitizer (B).

2. A positive photoresist composition comprising an alkali-soluble novolak resin
(A') containing a structural unit (a1) represented by a general formula (I) shown below:

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[wherein, R<sup>1</sup> represents an alkylene group of 1 to 5 carbon atoms, R<sup>2</sup> represents a hydrogen atom, a hydroxyl group, or an alkyl group of 1 to 4 carbon atoms, and m represents an integer of 1 to 3], and a structural unit (a2) represented by a general formula (II) shown below:

$$\begin{array}{c|c}
OH \\
\hline
 & H_2 \\
\hline
 & R^3)_n
\end{array}$$
(II)

[wherein, R<sup>3</sup> represents a hydrogen atom, a hydroxyl group, or an alkyl group of 1 to 4 carbon atoms, and n represents an integer of 1 to 3], wherein a portion of hydrogen atoms of said hydroxyl groups contained within said resin are substituted with 1,2-naphthoquinonediazidesulfonyl groups.

- 3. A positive photoresist composition according to claim 2, further comprising a photosensitizer (B).
- 4. A method of forming a resist pattern comprising the steps of applying a positive photoresist composition according to any one of claim 1 through claim 3 to a substrate,

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conducting a prebake, performing selective exposure, and then performing alkali developing to form the resist pattern.